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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.
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08/994,038 12/18/97 YAMAZAKI

S 07977/208001

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MM91/1219

EXAMINER

COLEMAN, W

ART UNIT

PAPER NUMBER

2823

DATE MAILED:

12/19/00

Please find below and/or attached an Office communication concerning this application or proceeding.

Commissioner of Patents and Trademarks

Office Action Summary

Application No.

08/994,038

Applicant(s)

YAMAZAKI ET AL.

Examiner

W. David Coleman

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2823

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136 (a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 06 October 2000.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-23 is/are pending in the application.
- 4a) Of the above claim(s) 7-10 and 15 is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-6, 11-14 and 16-23 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claims _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are objected to by the Examiner.
- 11) ☐ The proposed drawing correction filed on _____ is: a) ☐ approved b) ☐ disapproved.
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. § 119

- 13) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d).
- a) ☒ All b) ☐ Some * c) ☐ None of:
1. ☒ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgement is made of a claim for domestic priority under 35 U.S.C. & 119(e).

Attachment(s)

- 15) ☐ Notice of References Cited (PTO-892)
- 16) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 17) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) _____
- 18) ☐ Interview Summary (PTO-413) Paper No(s). _____
- 19) ☐ Notice of Informal Patent Application (PTO-152)
- 20) ☐ Other:

DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on October 6, 2000 has been entered.

Claim Rejections - 35 USC § 103

2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

3. Claims 1-6 and 11-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Mizutani et al. U.S. Patent 5,043,785 in view of Funakoshi et al. U.S. Patent 5,650,644.

Mizutani (785) discloses a semiconductor device substantially as claimed. Pertaining to claims 1 and 2, Mizutani (785) discloses a photosensor device for photoelectric conversion, and more particularly a photosensor device for photoelectric conversion such as CCD (column 1, lines 10-15). In FIG. 1, a thin semiconductor film 2 of n-type or i-type is formed on a substrate 1. Pertaining to claim 3, the substrate 1 is composed of a transparent substrate such as quartz or glass if the device receives the light through the substrate. The first semiconductor film can be

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composed of polycrystalline silicon or monocrystalline silicon. Pertaining to claims 4-6 and 11-14, the semiconductor film of n-type or i-type is doped with a p-type impurity, in predetermined areas 4, 24, 14, down to the substrate. As will be apparent from the equivalent circuit shown in FIG. 2, the photosensor device of the present embodiment is capable of switching the output from the photodiode 7 of high sensitivity with the high-speed MOS-FET 8 (column 3, lines 62-66). FIGS. 7 and 7A, conceptually illustrates the growth of a plurality of large grain polycrystalline film on a SiO₂ film 71. FIG. 7A shows a state in which nuclei 72 are formed; FIG. 7B shows a state in which the nuclei are grown into mutually contacting islands; and FIG. 7C shows a state in which a continuous film 73 is obtained by further growth, which is equivalent to Applicants crystalline semiconductor film having a plurality of crystals extending in a crystal growth direction. Also, it is the direction of incident light on the semiconductor device. However, Mizutani (785) fails to disclose a plurality of photodetecting elements. Funakoshi (644) discloses a plurality of photodetecting elements on the same substrate. See FIG. 1a-1f, Funakoshi (644) discloses more than several rows of a horizontal charge coupled devices 27, 28 and 29 also known as HCCD and vertical charge coupled devices 31 known as VCCD. In view of Funakoshi (644) it would have been obvious to incorporate a plurality of horizontal and vertical photodetecting element which are merely charge coupled devices (CCD's) into the Mizutani (785) semiconductor device to increase sensitivity, reduce design and manufacturing cost of a CCD and improve charge transfer.

4. Claims 16 and 19 are rejected under 35 U.S.C. 103(a) as being unpatentable over Zhang et al. U.S. Patent 5,604,360 in view of Mizutani et al. U.S. Patent 5,043,785.

Zhang (360) discloses a semiconductor device substantially as claimed. See **FIGS. 2A-2D**.

FIG. 1 is a top plan view showing a construction of a liquid crystal display of the embodiment of the present invention in outline, wherein a picture element section **10** having a plurality of picture element electrodes provided in matrix (not shown) and a peripheral circuit **20** as a driving circuit for driving each of the picture element electrodes are shown. A silicon oxide base film **102** is formed on a glass substrate, an amorphous silicon film **104** is arranged on top of silicon oxide **102**. Crystal grows in a lateral direction (direction parallel to the substrate) from the region **100** as shown by arrow **105** in the peripheral region of the region **100**. However, Zhang (360) fails to disclose a MOS capacitor for charge transfer. Mizutani (785) discloses a semiconductor device with a MOS capacitor. See **FIGS. 3 and 4**, an n-type semiconductor film **2** is doped with boron to simultaneously form P⁺ areas within a sensor area **4**, source and drain areas **14**, **24** and a MOS capacitance area **34**. Then, after the formation of gate insulator films, a gate **16** of the MOS capacitance and a gate **6** of the MOSFET are formed. In view of Mizutani (785) it would have been obvious to incorporate a MOS capacitor in the Zhang (360) semiconductor device for photoelectric conversion.

5. Pertaining to claims 17, 18 and 20-23 are rejected under 35 U.S.C. 103(a) as being unpatentable over Zhang et al. U.S. Patent 5,604,360 in view of Mizutani et al. U.S. Patent 5,043,785.

Zhang (360) discloses a semiconductor device substantially as claimed as discussed in claims 16 and 19 above. However, Zhang (360) does not disclose a quartz substrate or image sensor.

Mizutani (785) discloses a quartz substrate. In **FIG. 1**, a thin semiconductor film **2** of n-type or I-type is formed on a substrate **1**. The substrate **1** is composed of a transparent substrate such as

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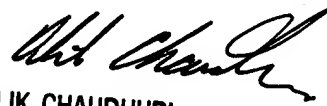
quartz if the device receives the light through the substrate. In view of Mizutani (785) it would have been obvious to incorporate quartz substrate in the Zhang (360) semiconductor device for use as an image sensor because the device receives light through the substrate (column 3, line 4).

Conclusion

6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to W. David Coleman whose telephone number is (703) 305-0004. The examiner can normally be reached on Monday-Friday from 9:00 AM to 5:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy, can be reached on (703) 308-4918. The fax phone number for the organization where this application or proceeding is assigned is (703) 308-7722.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.


OLIK CHAUDHURI
SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 2800